

**NOT RECOMMENDED FOR NEW DESIGNS  
POSSIBLE SUBSTITUTE PRODUCT  
CA3127, HFA3127**

**High-Frequency NPN Transistor Array For Low-Power Applications at Frequencies Up to 1.5GHz**

The CA3227 consists of five general purpose silicon NPN transistors on a common monolithic substrate. Each of the transistors exhibits a value of  $f_T$  in excess of 3GHz, making them useful from DC to 1.5GHz. The monolithic construction of these devices provides close electrical and thermal matching of the five transistors.

**Ordering Information**

PART NUMBER (BRAND)	TEMP. RANGE (°C)	PACKAGE	PKG. NO.
CA3227M (3227)	-55 to 125	16 Ld SOIC	M16.15
CA3227M96 (3227)	-55 to 125	16 Ld SOIC Tape and Reel	M16.15

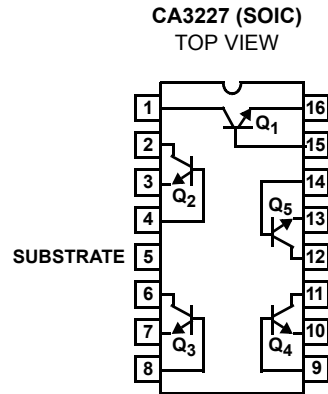
**Features**

- Gain-Bandwidth Product ( $f_T$ ) ..... >3GHz
- Five Transistors on a Common Substrate

**Applications**

- VHF Amplifiers
- VHF Mixers
- Multifunction Combinations - RF/Mixer/Oscillator
- IF Converter
- IF Amplifiers
- Sense Amplifiers
- Synthesizers
- Synchronous Detectors
- Cascade Amplifiers

**Pinout**



**Absolute Maximum Ratings**

Collector to Emitter Voltage ( $V_{CEO}$ ) ..... 8V  
 Collector to Base Voltage ( $V_{CBO}$ ) ..... 12V  
 Collector to Substrate Voltage ( $V_{CIO}$ , Note 1) ..... 20V  
 Collector Current ( $I_C$ ) ..... 20mA

**Operating Conditions**

Temperature Range ..... -55°C to 125°C

**Thermal Information**

Thermal Resistance (Typical, Note 2)  $\theta_{JA}$  (°C/W)  
 16 Ld SOIC Package ..... 185  
 Maximum Power Dissipation (Any One Transistor) ..... 85mW  
 Maximum Junction Temperature (Die) ..... 175°C  
 Maximum Junction Temperature (Plastic Package) ..... 150°C  
 Maximum Storage Temperature Range ..... -65°C to 150°C  
 Maximum Lead Temperature (Soldering 10s) ..... 300°C  
 (SOIC - Lead Tips Only)

*CAUTION: Stresses above those listed in "Absolute Maximum Ratings" may cause permanent damage to the device. This is a stress only rating and operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied.*

NOTES:

1. The collector of each transistor of these devices is isolated from the substrate by an integral diode. The substrate (Terminal 5) must be connected to the most negative point in the external circuit to maintain isolation between transistors and to provide for normal transistor action.
2.  $\theta_{JA}$  is measured with the component mounted on a low effective thermal conductivity test board in free air. See Tech Brief TB379 for details.

**Electrical Specifications**  $T_A = 25^\circ\text{C}$

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNITS
<b>DC CHARACTERISTICS FOR EACH TRANSISTOR</b>						
Collector to Base Breakdown Voltage	$V_{(BR)CBO}$	$I_C = 10\mu\text{A}, I_E = 0$	12	20	-	V
Collector to Emitter Breakdown Voltage	$V_{(BR)CEO}$	$I_C = 1\text{mA}, I_B = 0$	8	10	-	V
Collector to Substrate Breakdown Voltage	$V_{(BR)CIO}$	$I_{C1} = 10\mu\text{A}, I_B = 0, I_E = 0$	20	-	-	V
Emitter Cutoff Current (Note 3)	$I_{EBO}$	$V_{EB} = 4.5\text{V}, I_C = 0$	-	-	10	$\mu\text{A}$
Collector Cutoff Current	$I_{CEO}$	$V_{CE} = 5\text{V}, I_B = 0$	-	-	1	$\mu\text{A}$
Collector Cutoff Current	$I_{CBO}$	$V_{CB} = 8\text{V}, I_E = 0$	-	-	100	nA
DC Forward Current Transfer Ratio	$h_{FE}$	$V_{CE} = 6\text{V}$	$I_C = 10\text{mA}$	-	110	-
			$I_C = 1\text{mA}$	40	150	-
			$I_C = 0.1\text{mA}$	-	150	-
Base to Emitter Voltage	$V_{BE}$	$V_{CE} = 6\text{V}$	0.62	0.71	0.82	V
Collector to Emitter Saturation Voltage	$V_{CE\text{ SAT}}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	-	0.13	0.50	V
Base to Emitter Saturation Voltage	$V_{BE\text{ SAT}}$	$I_C = 10\text{mA}, I_B = 1\text{mA}$	0.74	-	0.94	V

NOTE:

3. On small-geometry, high-frequency transistors, it is very good practice never to take the Emitter Base Junction into reverse breakdown. To do so may permanently degrade the  $h_{FE}$ . Hence, the use of  $I_{EBO}$  rather than  $V_{(BR)EBO}$ . These devices are also susceptible to damage by electrostatic discharge and transients in the circuits in which they are used. Moreover, CMOS handling procedures should be employed.

# CA3227

## Electrical Specifications $T_A = 25^{\circ}\text{C}$ , 200MHz, Common Emitter, Typical Values Intended Only for Design Guidance

PARAMETER	SYMBOL		TEST CONDITIONS	TYPICAL VALUES	UNITS
<b>DYNAMIC CHARACTERISTICS FOR EACH TRANSISTOR</b>					
Input Admittance	$Y_{11}$	$b_{11}$	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	4	mS
		$g_{11}$		0.75	mS
Output Admittance	$Y_{22}$	$b_{22}$	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	2.7	mS
		$g_{22}$		0.13	mS
Forward Transfer Admittance	$Y_{21}$	$Y_{21}$	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	29.3	mS
		$\theta_{21}$		-33	Degrees
Reverse Transfer Admittance	$Y_{12}$	$Y_{12}$	$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	0.38	mS
		$\theta_{12}$		-97	Degrees
Input Admittance	$Y_{11}$	$b_{11}$	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$	4.8	mS
		$g_{11}$		2.85	mS
Output Admittance	$Y_{22}$	$b_{22}$	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$	2.75	mS
		$g_{22}$		0.9	mS
Forward Transfer Admittance	$Y_{21}$	$Y_{21}$	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$	95	mS
		$\theta_{21}$		-62	Degrees
Reverse Transfer Admittance	$Y_{12}$	$Y_{12}$	$I_C = 10\text{mA}, V_{CE} = 5\text{V}$	0.39	mS
		$\theta_{12}$		-97	Degrees
Small Signal Forward Current Transfer Ratio	$h_{21}$		$I_C = 1\text{mA}, V_{CE} = 5\text{V}$	7.1	
			$I_C = 10\text{mA}, V_{CE} = 5\text{V}$	17	
<b>TYPICAL CAPACITANCE AT 1MHz, THREE-TERMINAL MEASUREMENT</b>					
Collector to Base Capacitance	$C_{CB}$		$V_{CB} = 6\text{V}$	0.3	pF
Collector to Substrate Capacitance	$C_{CI}$		$V_{CI} = 6\text{V}$	1.6	pF
Collector to Emitter Capacitance	$C_{CE}$		$V_{CE} = 6\text{V}$	0.4	pF
Emitter to Base Capacitance	$C_{EB}$		$V_{EB} = 3\text{V}$	0.75	pF

## Spice Model (Spice 2G.6)

.model NPN

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+      BF = 2.610E + 02      BR = 4.401E + 00      IS = 6.930E - 16      RB = 130.0E + 00
+      RC = 1.000E + 01      RE = 7.396E - 01      VA = 6.300E + 01      VB = 2.208E + 00
+      IK = 1.000E - 01      ISE = 1.87E - 14      NE = 1.653E + 00      IKR = 1.000E - 02
+      ISC = 9.25E - 14      NC = 1.333E + 00      TF = 1.775E - 11      TR = 1.000E - 09
+      CJS = 1.800E - 12      CJE = 1.010E - 12      PE = 8.350E - 01      ME = 4.460E - 01
+      CJC = 9.100E - 13      PC = 3.850E - 01      MC = 2.740E - 01      KF = 0.000E + 00
+      AF = 1.000E + 00      EF = 1.000E + 00      FC = 5.000E - 01      PJS = 5.410E - 01
+      MJS = 3.530E - 01      RBM = 30.00      RBV = 100      IRB = 0.00

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Please Note: No measurements have been made to model the reverse AC operation (tr is an estimation).

Typical Performance Curves

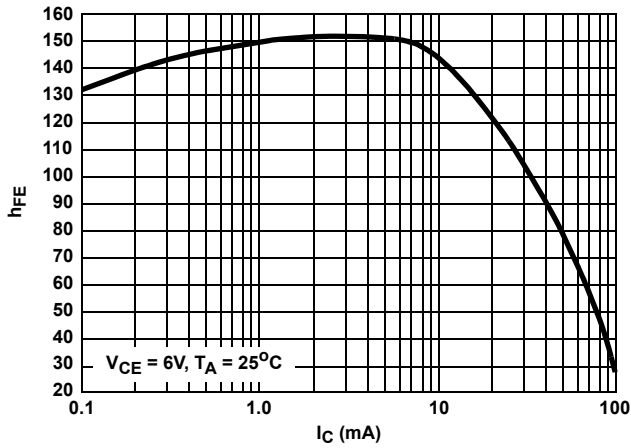


FIGURE 1.  $h_{FE}$  vs COLLECTOR CURRENT

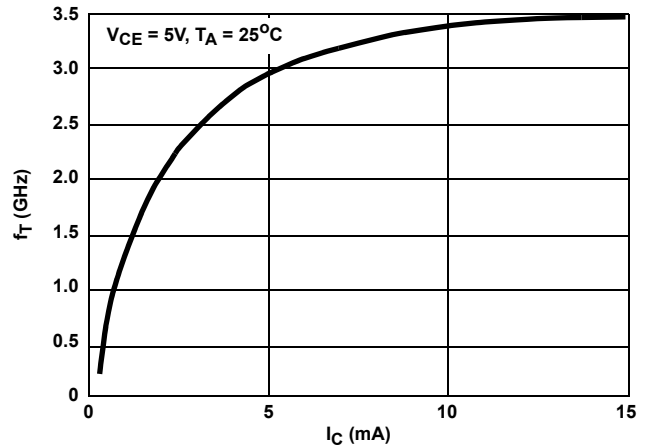


FIGURE 2.  $f_T$  vs COLLECTOR CURRENT

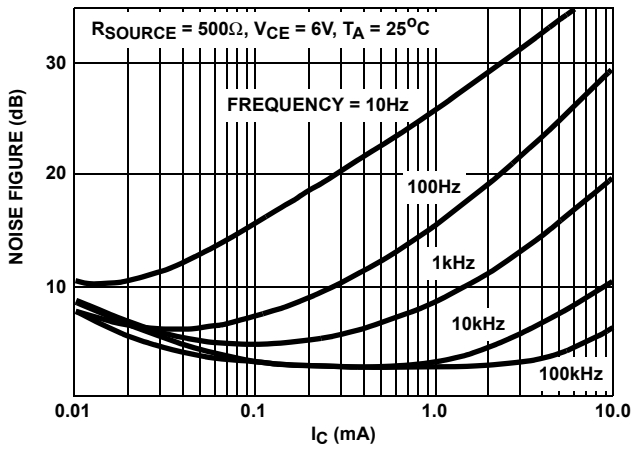


FIGURE 3. NOISE FIGURE vs COLLECTOR CURRENT

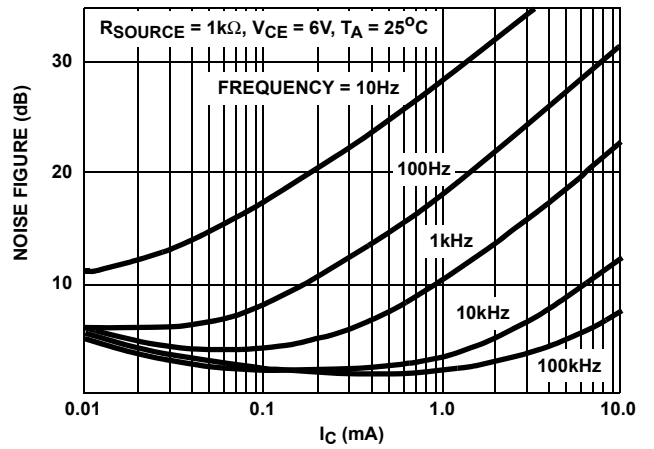


FIGURE 4. NOISE FIGURE vs COLLECTOR CURRENT

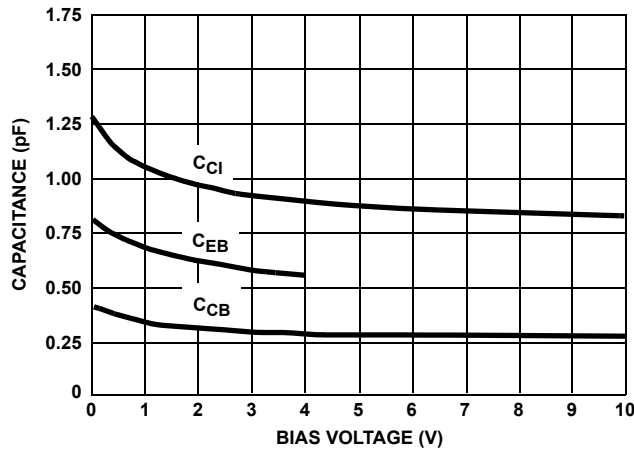


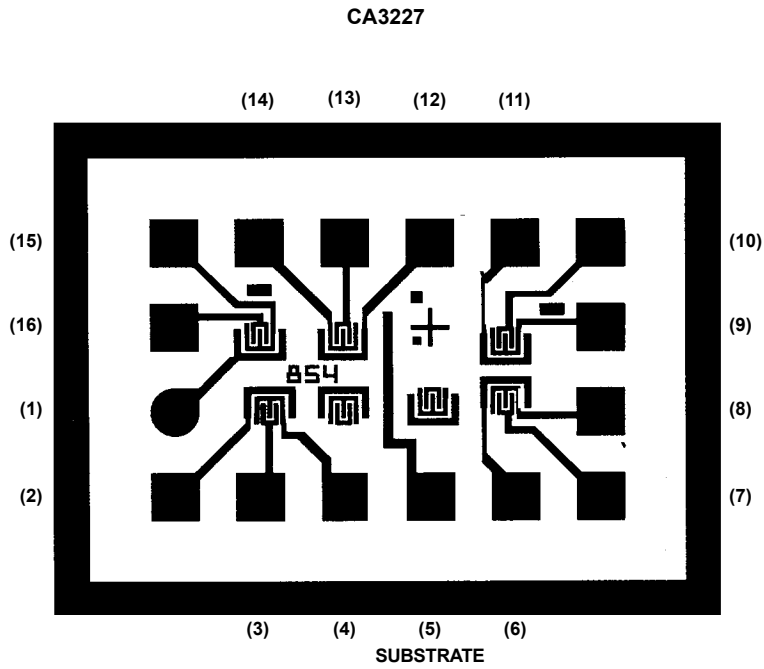
FIGURE 5. CAPACITANCE vs BIAS VOLTAGE

**Die Characteristics**

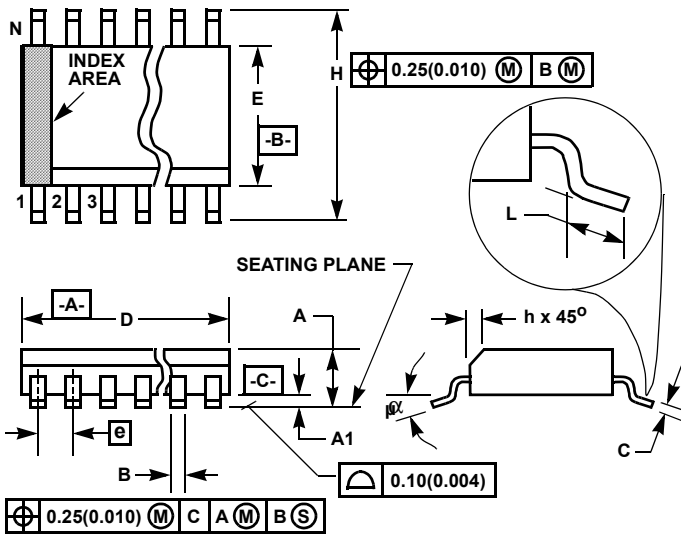
**DIE DIMENSIONS:**

46 mils x 32 mils

**Metallization Mask Layout**



Small Outline Plastic Packages (SOIC)



**M16.15** (JEDEC MS-012-AC ISSUE C)  
**16 LEAD NARROW BODY SMALL OUTLINE PLASTIC PACKAGE**

SYMBOL	INCHES		MILLIMETERS		NOTES
	MIN	MAX	MIN	MAX	
A	0.0532	0.0688	1.35	1.75	-
A1	0.0040	0.0098	0.10	0.25	-
B	0.013	0.020	0.33	0.51	9
C	0.0075	0.0098	0.19	0.25	-
D	0.3859	0.3937	9.80	10.00	3
E	0.1497	0.1574	3.80	4.00	4
e	0.050 BSC		1.27 BSC		-
H	0.2284	0.2440	5.80	6.20	-
h	0.0099	0.0196	0.25	0.50	5
L	0.016	0.050	0.40	1.27	6
N	16		16		7
$\alpha$	0°	8°	0°	8°	-

NOTES:

1. Symbols are defined in the "MO Series Symbol List" in Section 2.2 of Publication Number 95.
2. Dimensioning and tolerancing per ANSI Y14.5M-1982.
3. Dimension "D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion and gate burrs shall not exceed 0.15mm (0.006 inch) per side.
4. Dimension "E" does not include interlead flash or protrusions. Interlead flash and protrusions shall not exceed 0.25mm (0.010 inch) per side.
5. The chamfer on the body is optional. If it is not present, a visual index feature must be located within the crosshatched area.
6. "L" is the length of terminal for soldering to a substrate.
7. "N" is the number of terminal positions.
8. Terminal numbers are shown for reference only.
9. The lead width "B", as measured 0.36mm (0.014 inch) or greater above the seating plane, shall not exceed a maximum value of 0.61mm (0.024 inch).
10. Controlling dimension: MILLIMETER. Converted inch dimensions are not necessarily exact.

Rev. 0 12/93

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